

Jiarui Gong

List of Publications by Year in descending order

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Version: 2024-02-01

10
papers

197
citations

1162367

8
h-index

1473754

9
g-index

11
all docs

11
docs citations

11
times ranked

242
citing authors

#	ARTICLE	IF	CITATIONS
1	226-nm AlGaIn/AlN UV LEDs using p-type Si for hole injection and UV reflection. Applied Physics Letters, 2018, 113, .	1.5	59
2	229-nm UV LEDs on aluminum nitride single crystal substrates using p-type silicon for increased hole injection. Applied Physics Letters, 2018, 112, .	1.5	52
3	Reduction of Leakage Current in GaN Schottky Diodes Through Ultraviolet/Ozone Plasma Treatment. IEEE Electron Device Letters, 2019, 40, 1796-1799.	2.2	18
4	P-type silicon as hole supplier for nitride-based UVC LEDs. New Journal of Physics, 2019, 21, 023011.	1.2	16
5	AlGaIn/GaN Schottky-Gate HEMTs With UV/O ₃ -Treated Gate Interface. IEEE Electron Device Letters, 2020, 41, 1488-1491.	2.2	13
6	Influences of screw dislocations on electroluminescence of AlGaIn/AlN-based UVC LEDs. AIP Advances, 2019, 9, .	0.6	11
7	Fabrication of AlGaAs/GaAs/diamond heterojunctions for diamond-collector HBTs. AIP Advances, 2020, 10, .	0.6	11
8	Metal-Al ₂ O ₃ -GaN capacitors with an ultraviolet/ozone plasma-treated interface. Japanese Journal of Applied Physics, 2020, 59, 030908.	0.8	8
9	Influences of ALD Al ₂ O ₃ on the surface band-bending of c-plane, Ga-face GaN. Japanese Journal of Applied Physics, 2022, 61, 011003.	0.8	7
10	Toward Diamond-Collector Heterojunction Bipolar Transistors via grafted GaAs-Diamond n-p junction. , 2019, , .		2